

DIGITAL LOGIC

Chapter 7 Memory

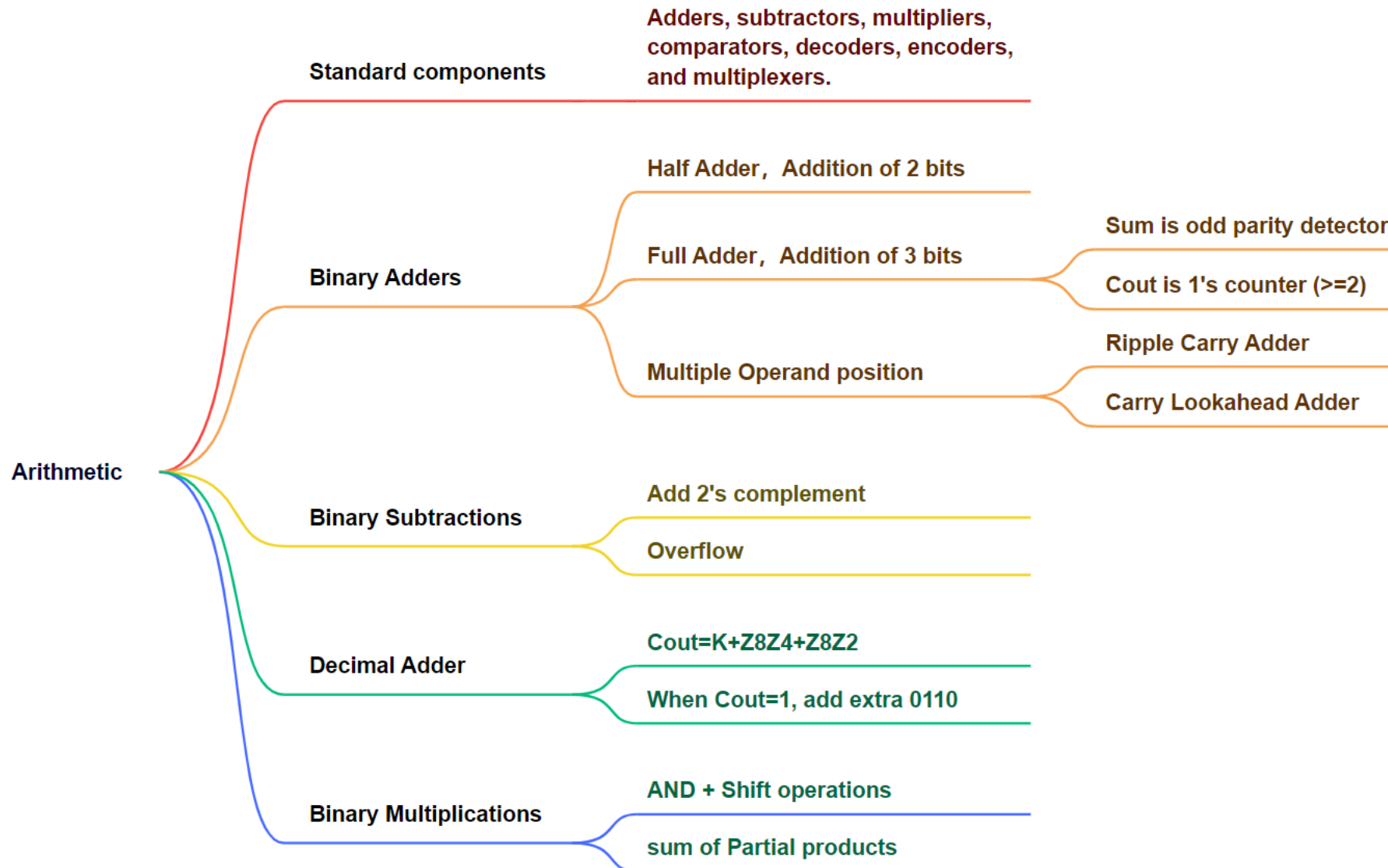
2024 Fall

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Today's Agenda

- Recap
 - Asynchronous Counter
 - Synchronous Counter
 - Binary counter
 - Ring counter
 - Johnson counter
 - Design a synchronous counter
- Context
 - RAM
 - ROM
 - PLA
 - FPGA
- Reading: Textbook, Chapter 7

Recap



Outline

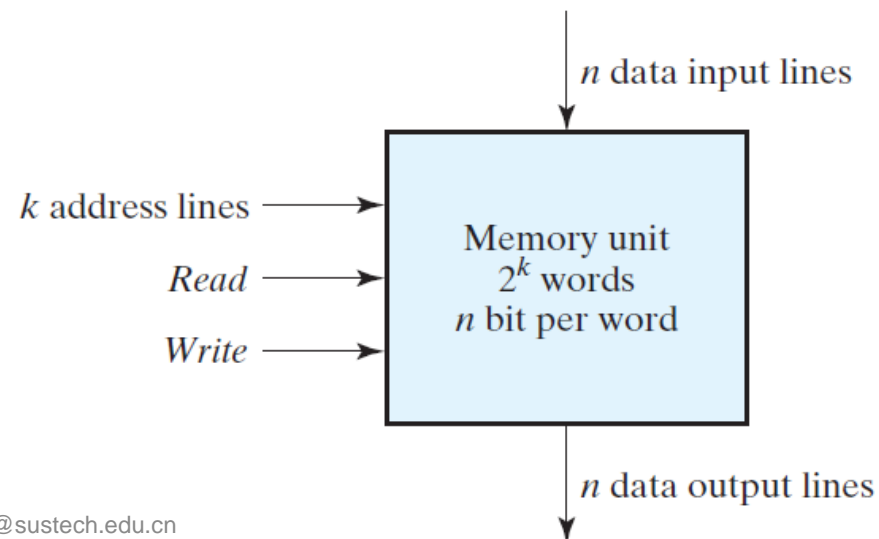
- Random-Access Memory
- Memory Decoding
- Read-Only Memory
- Programmable Logic Array
- Sequential Programmable Devices-FPGA

Memory Unit

- A collection of storage cells together with associated circuits needed to transfer information in and out of storage
- RAM: Random-Access Memory
 - Volatile (memory units that lose stored information when power is turned off)
 - To accept new information for storage to be available later for use
 - read/write operation
- ROM: Read-Only Memory
 - Nonvolatile
 - The information inside can not be altered by writing
 - Programmable devices are specified by some hardware procedure

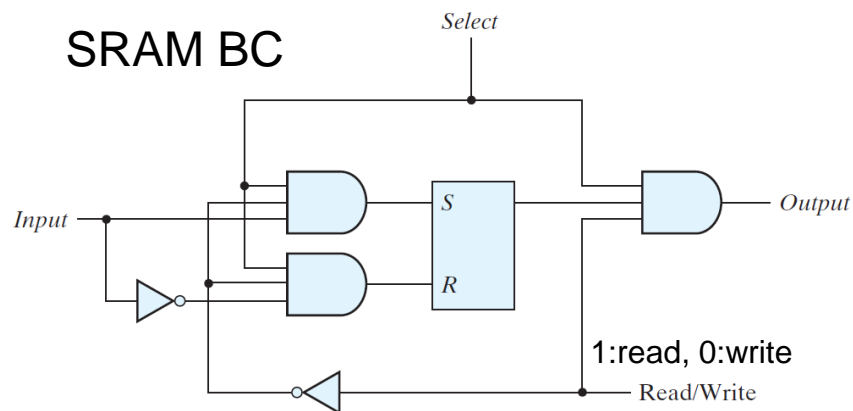
Random-Access Memory

- Characteristics
 - The time it takes to transfer data to or from any desired location is always the same.
 - A memory unit stored binary information in groups of bits (words)
 - The size of the RAM is $2^k \times n$ bits. It has k address lines, n input data lines and n output data lines.
 - For a commodity RAM, $n=8, 16, 32$ or 64 .
- The communication between a memory and its environment is achieved through
 - Data input lines
 - Data output lines
 - Address selection lines
 - Control lines (read and write)



Memory Content Array & Memory Cell

- A memory with k -bit address has 2^k words (depth)
 - (depth)x(width) memory
 - eg. 1K x 16 memory (1024x16 memory)
- A memory cell is also called a binary storage cell (BC)



Memory address		Memory content
Binary	Decimal	
0000000000	0	1011010101011101
0000000001	1	1010101110001001
0000000010	2	0000110101000110
	⋮	⋮
1111111101	1021	1001110100010100
1111111110	1022 2^k-2	0000110100011110
1111111111	1023 2^k-1	1101111000100101

k-bit address **n bits data**

Static RAM vs. Dynamic RAM

- A memory cell (MC) can be considered as a clocked D latch with an AND gate and an output driver
- For a **static RAM (SRAM)**, MC is constructed by 6 transistors
 - using cross-coupled inverters to serve as a latch
 - and implementing the input AND gate and the output driver with one transistor each.
- For a **dynamic RAM (DRAM)**, MC is constructed by only 1 transistor
 - The latch is implemented by a capacitor.
 - It needs to be refreshed periodically (read and write back).
 - It has high density (therefore low cost)

Write and Read Operation

- Write operation
 - Apply the binary address to the address lines
 - Apply the data bits to the data input lines
 - Activate the write input (0)
- Read operation
 - Apply the binary address to the address lines
 - Activate the read input (1)

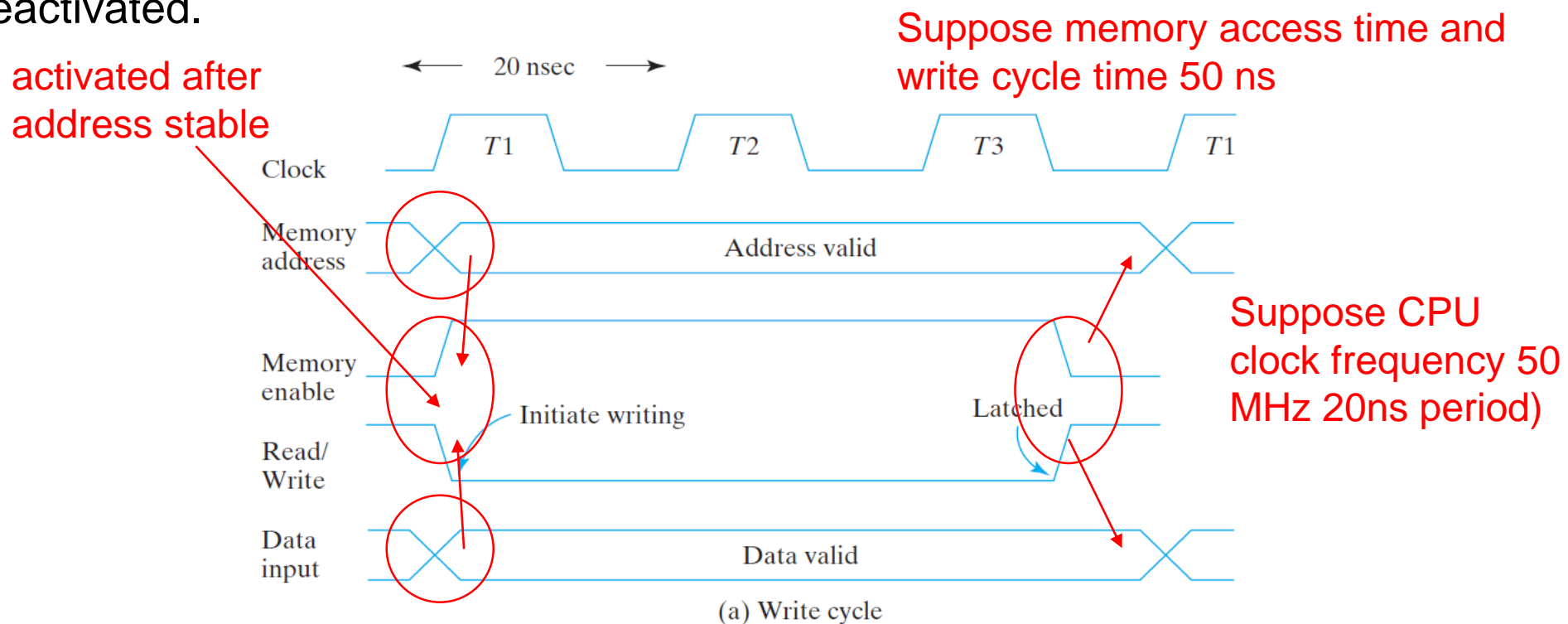
Memory Enable	Read/Write	Memory Operation
0	X	None
1	0	Write to selected word
1	1	Read from selected word

Timing Waveforms

- The operation of the memory unit is controlled by an external device such as a CPU
- The access time is the time required to select a word and read it
- The write cycle time is the time required to complete a write operation
- Read and write operations must be controlled by CPU and be synchronized with an external clock.

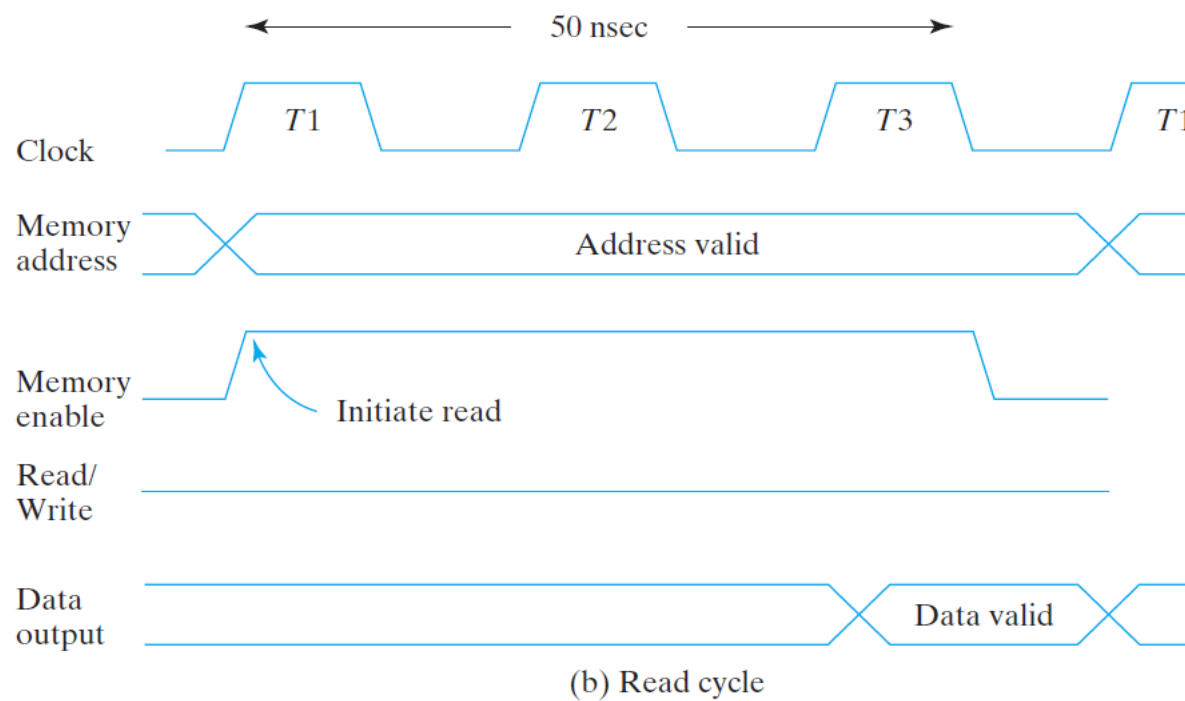
Timing Waveforms

- A write cycle
 - T1: providing the address and input data to the memory, and the write/read control signal
 - Address bus and read/write control must stay active for 50ns
 - The address and data signal must remain stable for a short time after control signal is deactivated.



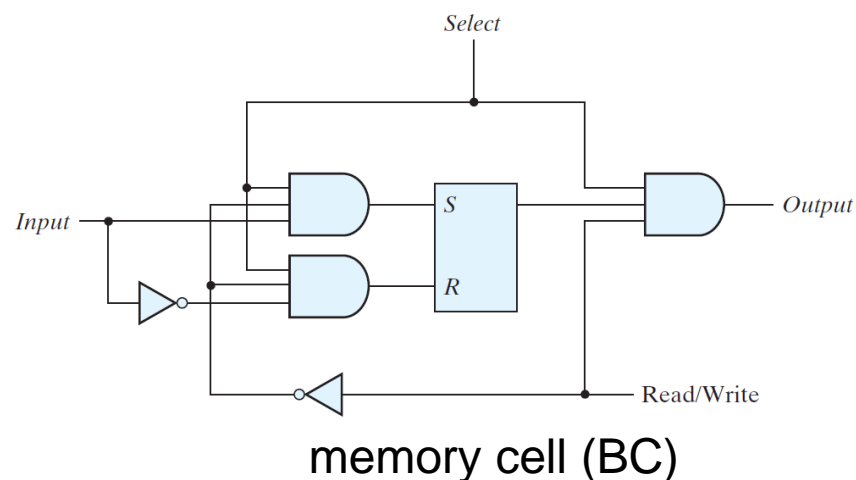
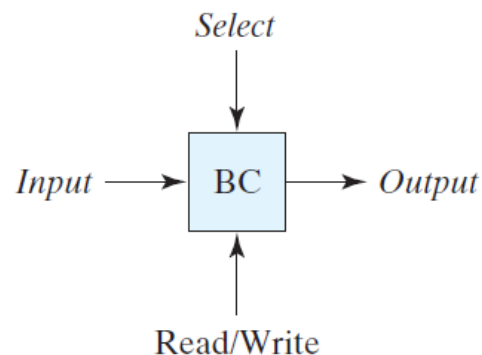
Timing Waveforms

- A read cycle



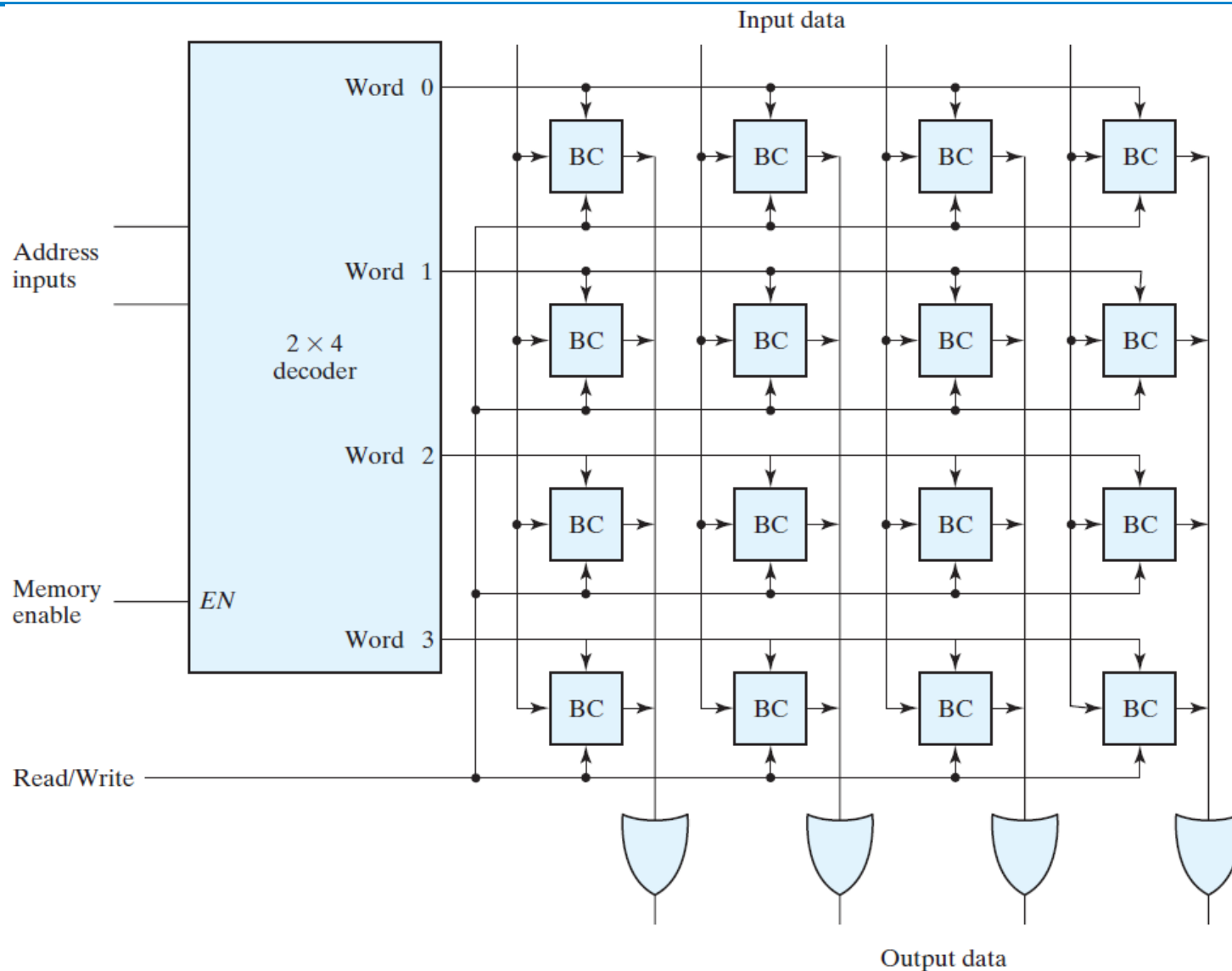
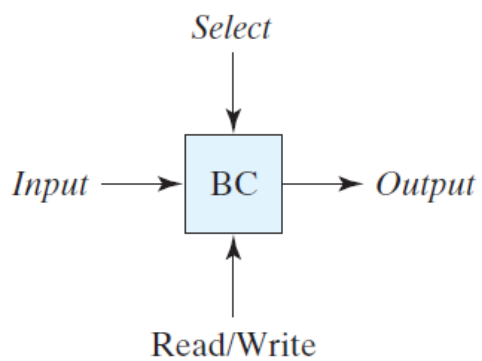
Memory Unit and Internal Construction

- A memory unit has two parts
 - The storage components (memory cell)
 - The decoding circuits to select the memory word
- A RAM of m (2^k) words and n bits per word
 - $m \times n$ binary storage cells
 - Decoding circuits to select individual words
 - k -to- 2^k decoder: address input to word line
 - Read/Write control
 - Input data/Output data



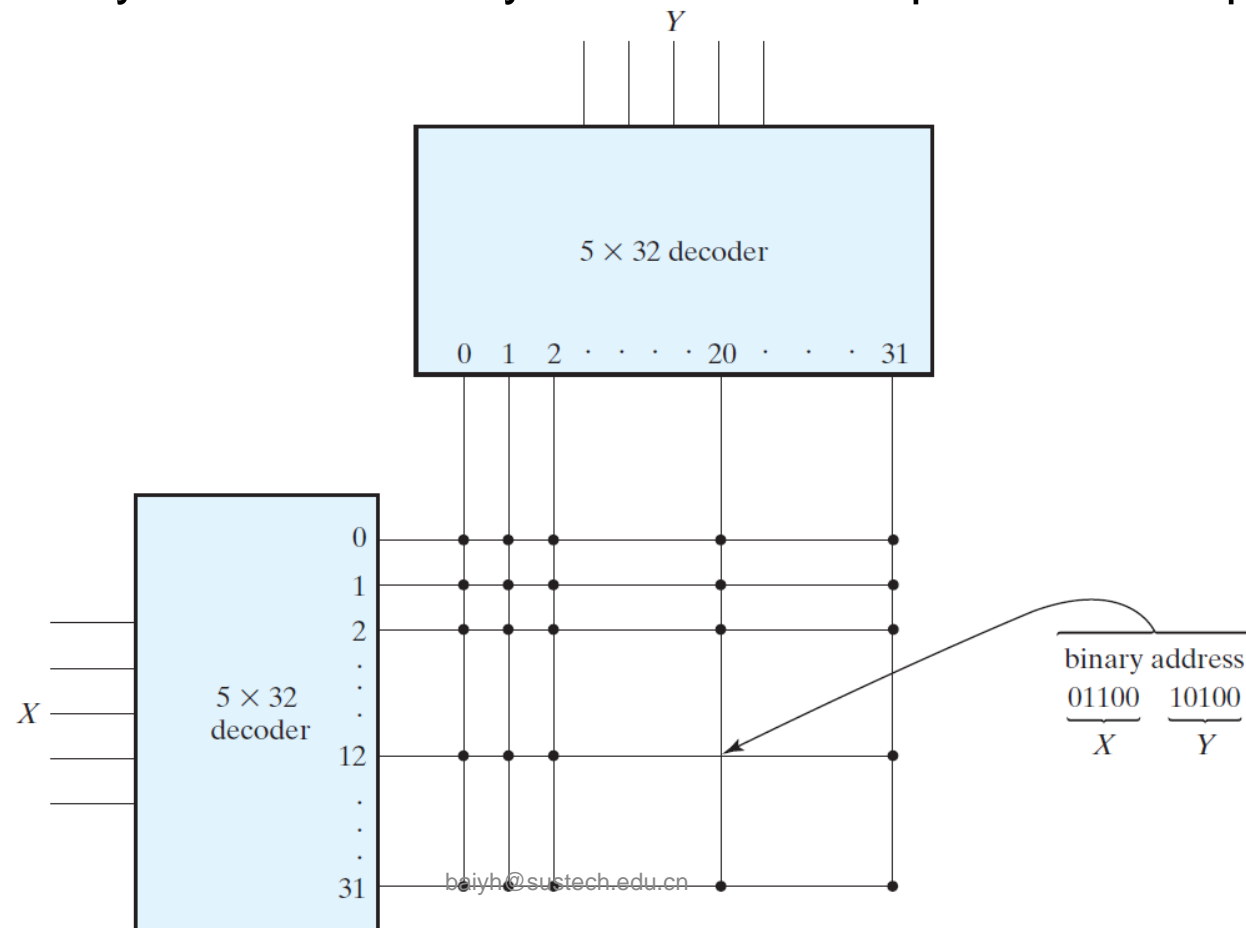
4x4 RAM

check the decoder
with enable input
in Chapter 4



Coincident Decoding

- A two-dimensional selection scheme
 - To reduce the complexity of the decoding circuits
 - To arrange the memory cells in an array that is close as possible to square

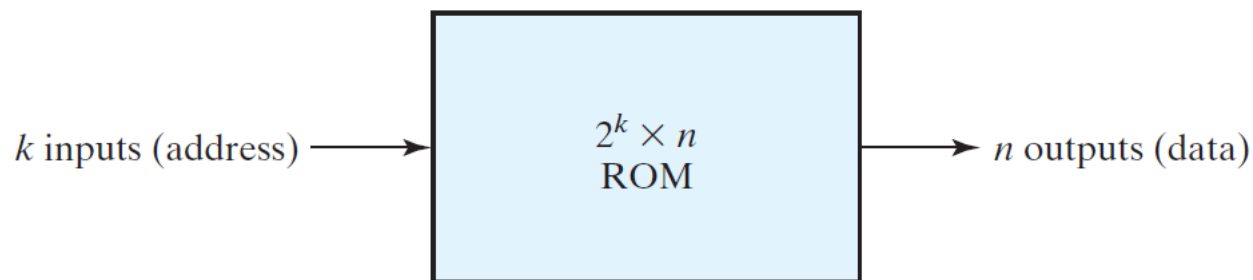


Coincident Decoding

- Example: 1k-word memory
 - A 10-to-1024 decoder
 - 1024 AND gates with 10 inputs per gate
 - Two 5-to-32 decoders
 - $2 \times (32 \text{ AND gates with 5 inputs per gate})$
 - Each word in the memory is selected by the coincidence between 1 of 32 rows and 1 of 32 columns for a total 1024 words
 - Two dimensional decoding structure reduces the circuit complexity and the cycle time of the memory

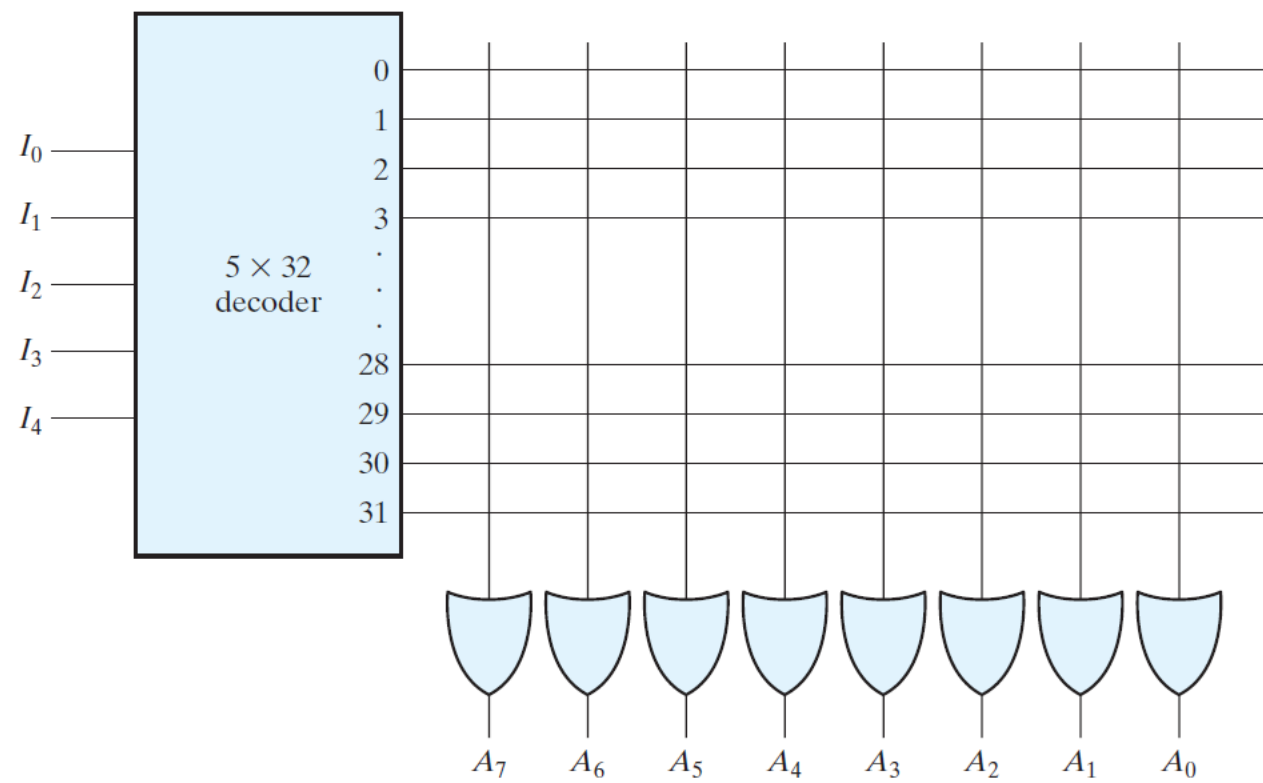
Read-Only Memory (ROM)

- ROM stores permanent binary information
- Once the pattern is established in the ROM, it stays within the unit, no matter power is on or off
- $2^k \times n$ ROM
 - k address input lines
 - enable input(s)



32x8 ROM

- 32 x 8 ROM ($2^5 \times 8$)
 - 5-to-32 decoder ($k=5$)
 - $32(2^5)$ outputs of the decoder are connected to each of the eight OR gates, which have $32(2^5)$ inputs
 - 32 x 8 internal programmable connections



ROM Programming

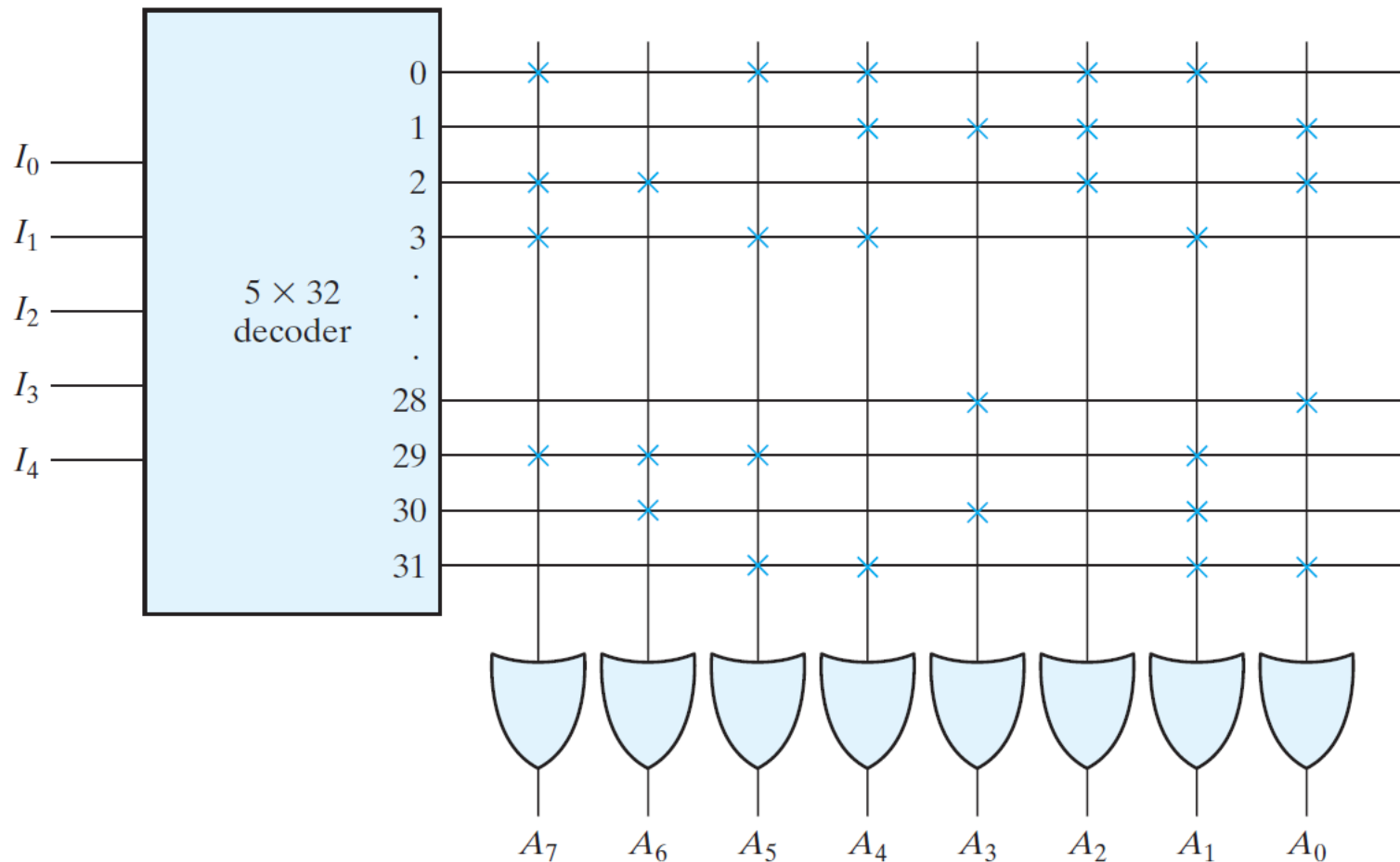
- PROM(Programmable ROM) with programmable interconnections
- close [1]: connected to high voltage
- open [0]: ground left
- A fuse that can be blown by applying a high voltage pulse

ROM Truth Table (Partial)

Inputs					Outputs							
I_4	I_3	I_2	I_1	I_0	A_7	A_6	A_5	A_4	A_3	A_2	A_1	A_0
0	0	0	0	0	1	0	1	1	0	1	1	0
0	0	0	0	1	0	0	0	1	1	1	0	1
0	0	0	1	0	1	1	0	0	0	1	0	1
0	0	0	1	1	1	0	1	1	0	0	1	0
		\vdots							\vdots			
1	1	1	0	0	0	0	0	0	1	0	0	1
1	1	1	0	1	1	1	1	0	0	0	1	0
1	1	1	1	0	0	1	0	0	1	0	1	0
1	1	1	1	1	0	0	1	1	0	0	1	1

ROM Programming

- ROM programming according to ROM table using fusing



Combinational Circuit Implementation

- The internal operation of ROM can be interpreted in two ways
 - A memory contains a fixed pattern of stored words
 - A unit that implements a combinational circuit as sum of minterms.
- ROM: a decoder + OR gates
 - a Boolean function = sum of minterms
 - Ex. $A_7(I_4, I_3, I_2, I_1, I_0) = \sum(0, 2, 3, \dots, 29)$
 - For an n-input, m-output combinational circuit
 - $2^n \times m$ ROM
- Design Procedure
 - Determine the size of ROM
 - Obtain the programming truth table of ROM
 - The truth table = the fuse pattern

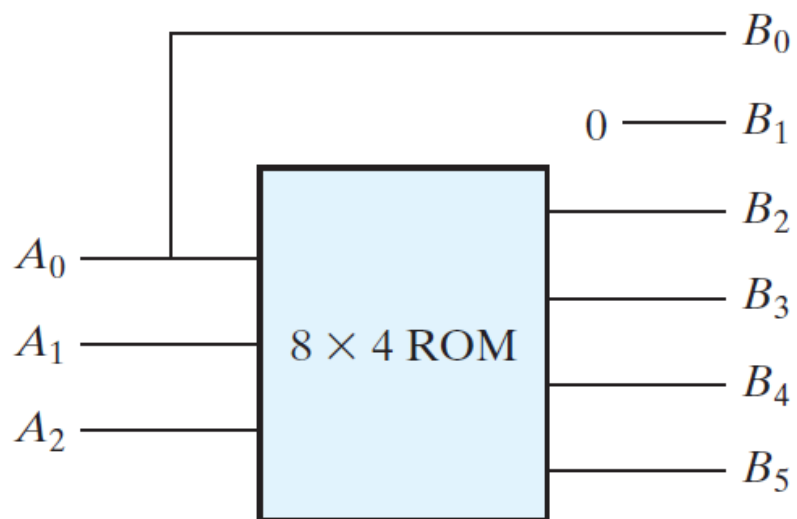
ROM Implementation

- A combinational circuit has 3 inputs, 6 outputs and the truth table, construct the circuit

Inputs			Outputs						Decimal
A_2	A_1	A_0	B_5	B_4	B_3	B_2	B_1	B_0	
0	0	0	0	0	0	0	0	0	0
0	0	1	0	0	0	0	0	1	1
0	1	0	0	0	0	1	0	0	4
0	1	1	0	0	1	0	0	1	9
1	0	0	0	1	0	0	0	0	16
1	0	1	0	1	1	0	0	1	25
1	1	0	1	0	0	1	0	0	36
1	1	1	1	1	0	0	0	1	49

$B_0=A_0$, $B_1=0$, leave only 8x4 ROM

ROM Implementation



(a) Block diagram

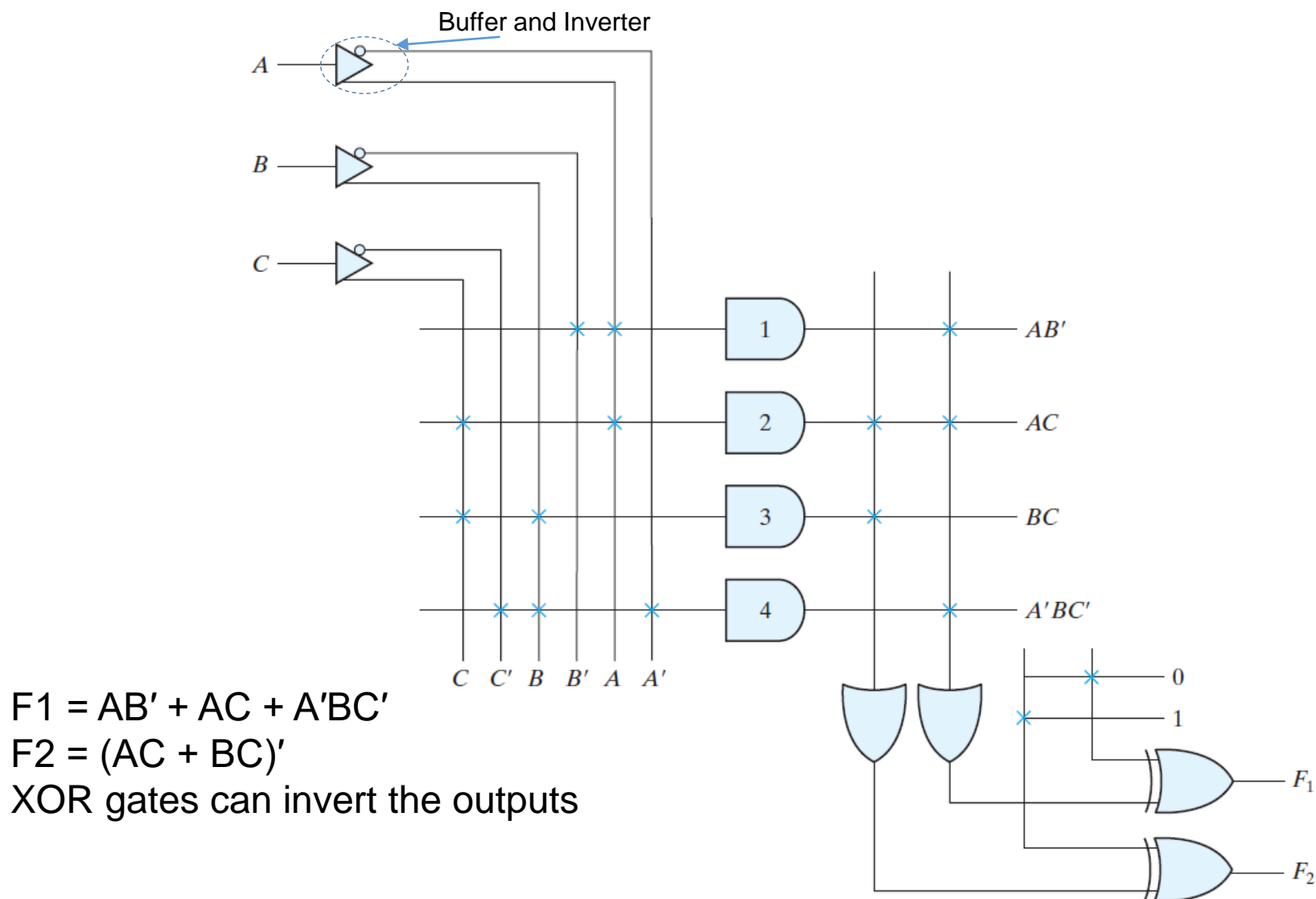
A_2	A_1	A_0	B_5	B_4	B_3	B_2
0	0	0	0	0	0	0
0	0	1	0	0	0	0
0	1	0	0	0	0	1
0	1	1	0	0	1	0
1	0	0	0	1	0	0
1	0	1	0	1	1	0
1	1	0	1	0	0	1
1	1	1	1	1	0	0

(b) ROM truth table

Programmable Logic Array

- PLA has two main parts
 - An array of programmable AND gates
 - Can generate any product terms of the inputs
 - An array of programmable OR gates
 - Can generate the sums of the products
- PLA is more flexible than PROM
 - PLA uses any combination of products while PROM uses sum of minterms
- PLA uses less circuits than PROM
 - Only the needed product terms are generated in PLA while all minterms must be generated in PROM

PLA



PLA

- Specify the fuse map
 - 1st col: list the product terms numerically
 - 2nd col: specify the required paths between inputs and AND gates
 - 3rd col: specify the required paths between AND gates and OR gates
 - (T)(C) stand for true or complement for programming XOR

PLA Programming Table

		Inputs			Outputs	
		A	B	C	(T) F_1	(C) F_2
AB'	1	1	0	—	1	—
AC	2	1	—	1	1	1
BC	3	—	1	1	—	1
$A'BC'$	4	0	1	0	1	—

Example

- Implement the following two Boolean functions with a PLA:
- $F_1(A, B, C) = \Sigma (0, 1, 2, 4)$
- $F_2(A, B, C) = \Sigma (0, 5, 6, 7)$
 - Both true and complement of the function should be simplified to check

$A \backslash BC$	00	01	11	10
0	1	1	1	1
1	1	0	1	0

$$F_1' = AB + AC + BC$$

$$F_1 = (AB + AC + BC)'$$

$A \backslash BC$	00	01	11	10
0	1	0	0	0
1	0	1	1	1

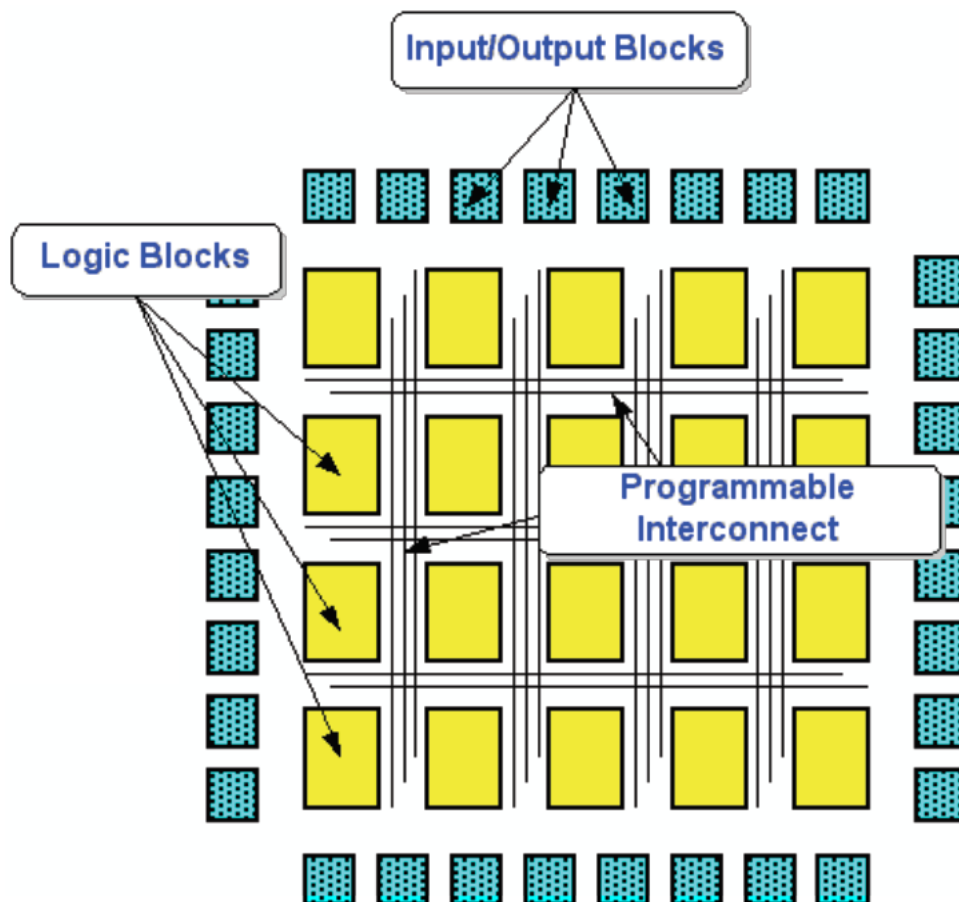
$$F_2 = AB + AC + A'B'C'$$

PLA programming table

	Product term	Inputs			Outputs	
		A	B	C	(C) F_1	(T) F_2
AB	1	1	1	–	1	1
AC	2	1	–	1	1	1
BC	3	–	1	1	1	–
$A'B'C'$	4	0	0	0	–	1

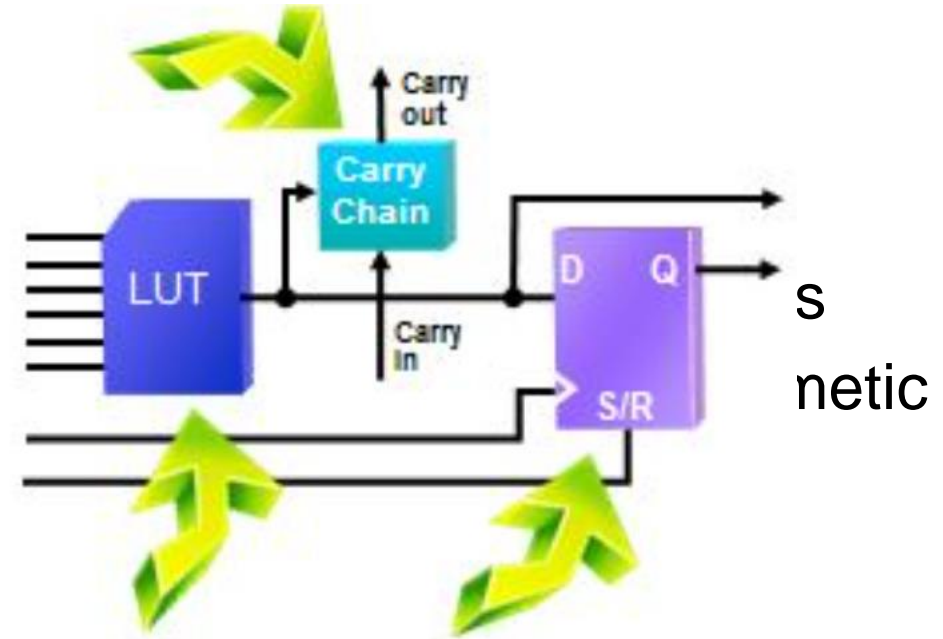
FPGA

- What is in the array? All sorts of stuff...
 - I/O Cells
 - Logic Cells
 - Memories
 - Microprocessors
 - Clock Management
 - High Speed I/O Transceivers
 - Programmable routing

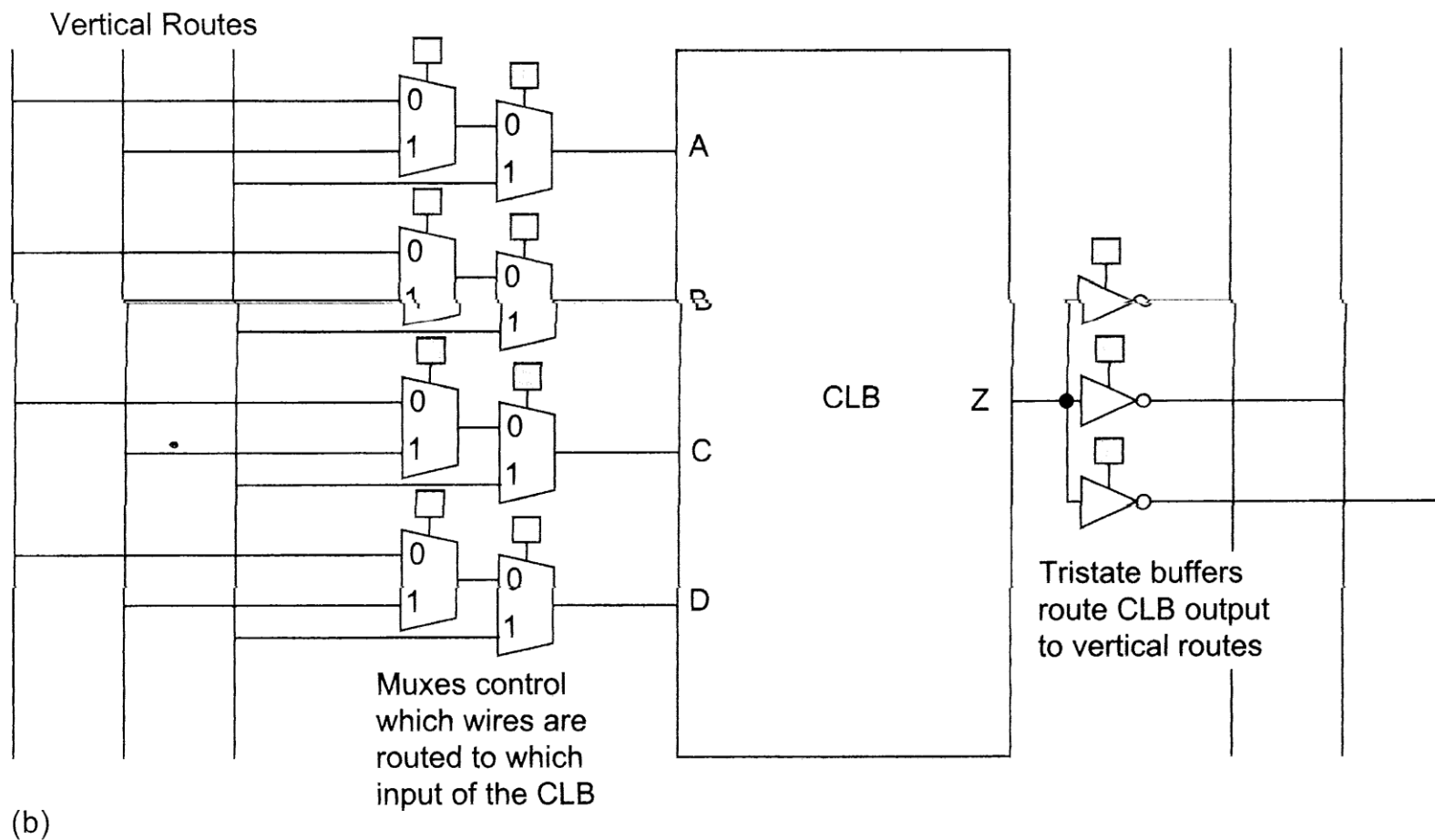


Simple FPGA Logic Cell

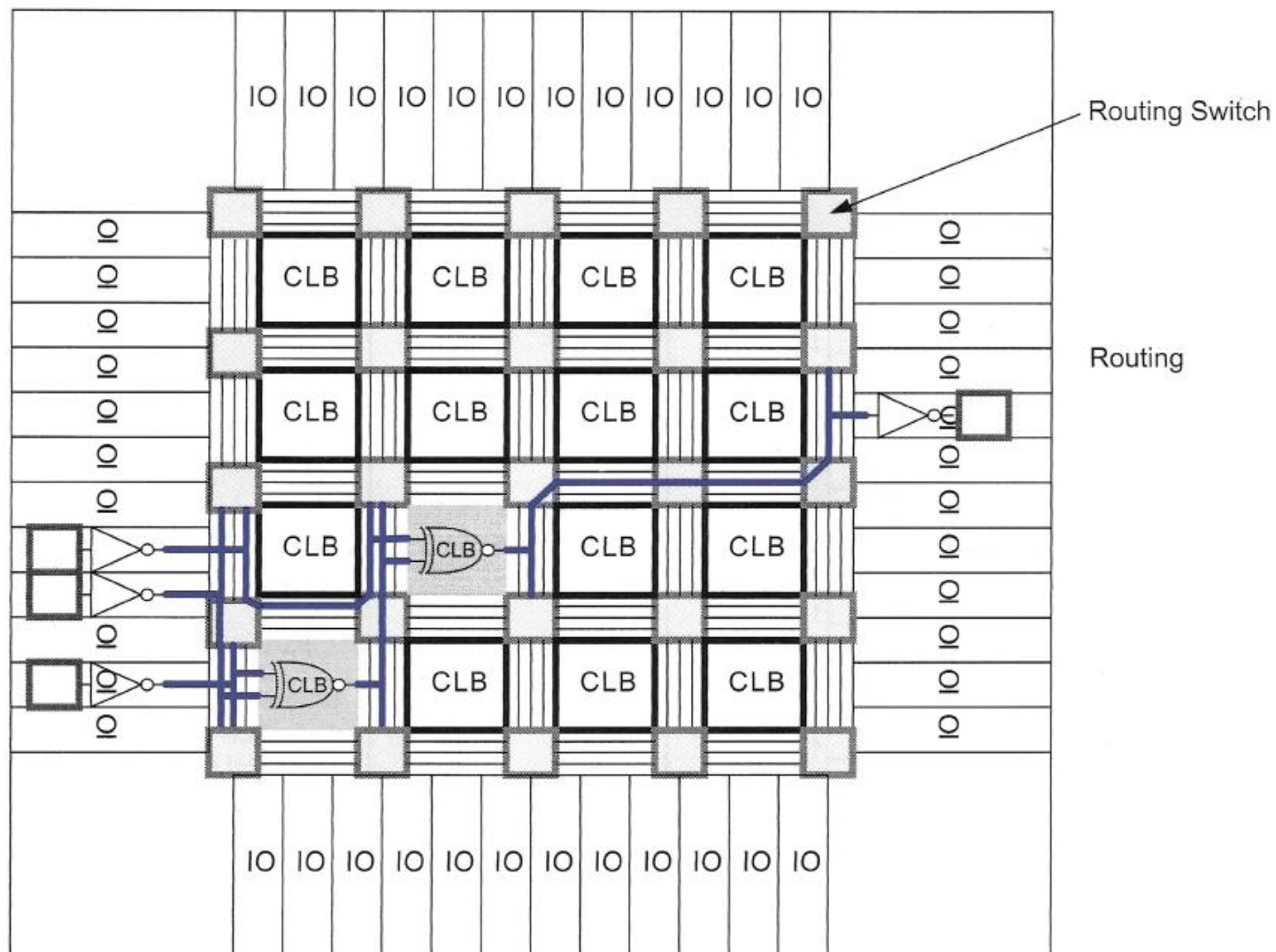
- Logic cells include
 - Combinatorial logic, arithmetic logic, and a register
- Combinatorial logic is implemented using LUTs
- Register functions can include latches, JK flip-flops, and D flip-flops
- Arithmetic logic is a dedicated carry chain for ripple-carry operations



Simple FPGA Routing Cell



Routed FPGA



JKFF FPGA implementation

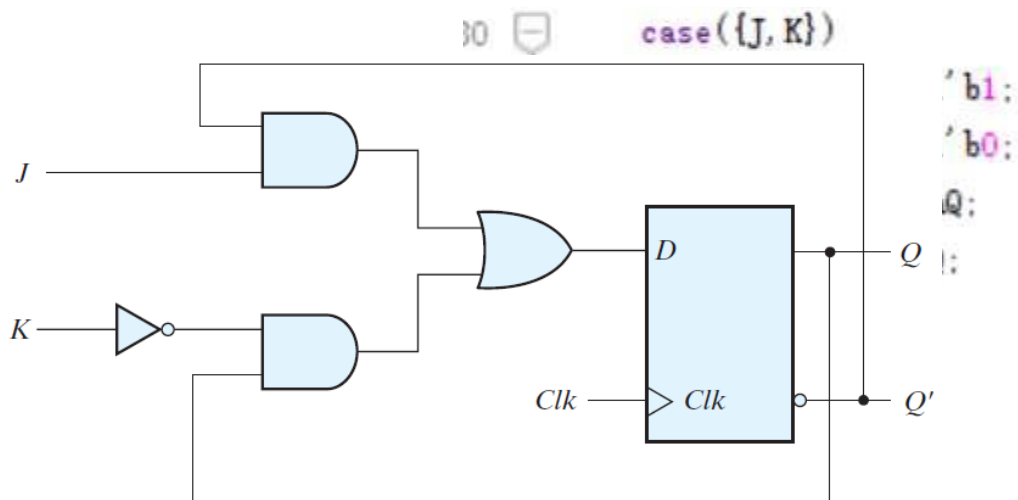
Characteristic table				J	K	Q(t)	Q(t+1)
JK Flip-Flop				0	0	0	0
J	K	Q(t + 1)		0	0	1	1
0	0	Q(t)	No change	0	1	0	0
0	1	0	Reset	0	1	1	0
1	0	1	Set	1	0	0	1
1	1	Q'(t)	Complement	1	0	1	1
				1	1	0	1
				1	1	1	0

Derive the Truth table



Characteristic equation of JKFF

$$Q(t+1) = JQ(t)' + K'Q(t)$$



JKFF FPGA implementation

